



ON Semiconductor®

FQPF16N25C

N-Channel QFET® MOSFET

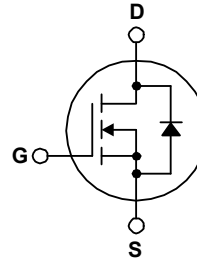
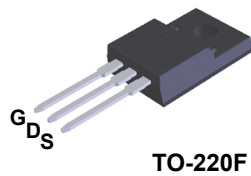
250 V, 15.6 A, 270 mΩ

Features

- 15.6 A, 250 V, $R_{DS(on)} = 270 \text{ m}\Omega$ (Max) @ $V_{GS} = 10 \text{ V}$, $I_D = 7.8 \text{ A}$
- Low Gate Charge (Typ. 41 nC)
- Low C_{rss} (Typ. 68 pF)
- 100% Avalanche Tested

Description

This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQPF16N25C	Unit
V_{DSS}	Drain to Source Voltage	250	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	15.6 *
		- Continuous ($T_C = 100^\circ\text{C}$)	9.8 *
I_{DM}	Drain Current	- Pulsed (Note 1)	62.4 *
V_{GSS}	Gate to Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	410	mJ
I_{AR}	Avalanche Current (Note 1)	15.6	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	13.9	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	43
		- Derate Above 25°C	0.34
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQPF16N25C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	2.89	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max	62.5	$^\circ\text{C}/\text{W}$

FQPF16N25C — N-Channel QFET® MOSFET

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQPF16N25C	FQPF16N25C	TO-220F	Tube	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	250	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.31	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 200\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 7.8\text{ A}$	--	0.22	0.27	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 7.8\text{ A}$	--	10.5	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	830	1080	pF
C_{oss}	Output Capacitance		--	170	220	pF
C_{rss}	Reverse Transfer Capacitance		--	68	89	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 125\text{ V}, I_D = 15.6\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 25\ \Omega$	--	15	40	ns
t_r	Turn-On Rise Time		--	130	270	ns
$t_{d(off)}$	Turn-Off Delay Time		--	135	280	ns
t_f	Turn-Off Fall Time		(Note 4)	--	105	220
Q_g	Total Gate Charge	$V_{DS} = 200\text{ V}, I_D = 15.6\text{ A},$ $V_{GS} = 10\text{ V}$	--	41	53.5	nC
Q_{gs}	Gate-Source Charge		--	5.6	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	22.7	--
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	15.6	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	62.4	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 15.6\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 15.6\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	260	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.47	--	μC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature
2. $L = 2.7\text{ mH}, I_{AS} = 15.6\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 15.6\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature

Typical Characteristics

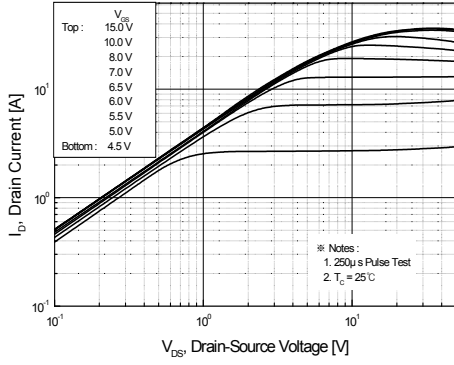


Figure 1. On-Region Characteristics

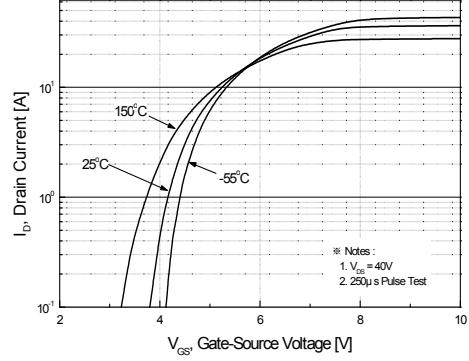


Figure 2. Transfer Characteristics

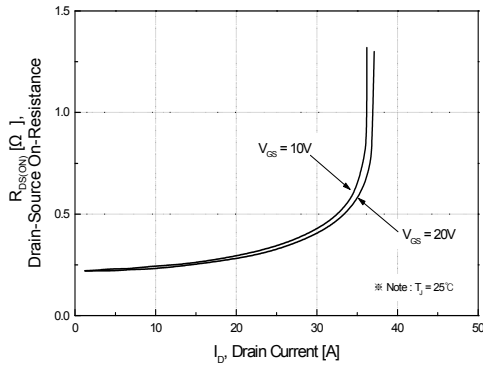


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

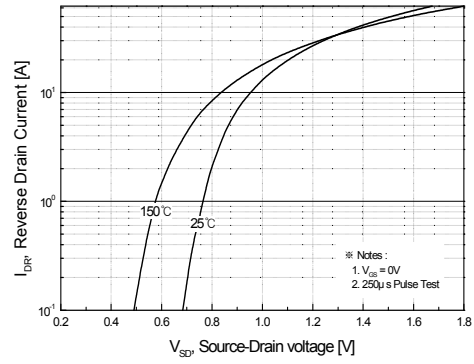


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

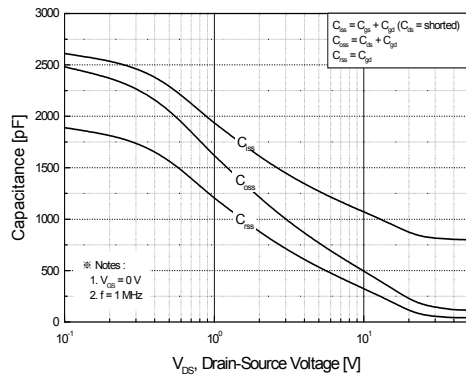


Figure 5. Capacitance Characteristics

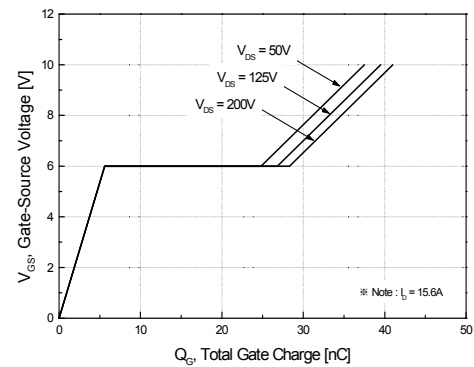


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

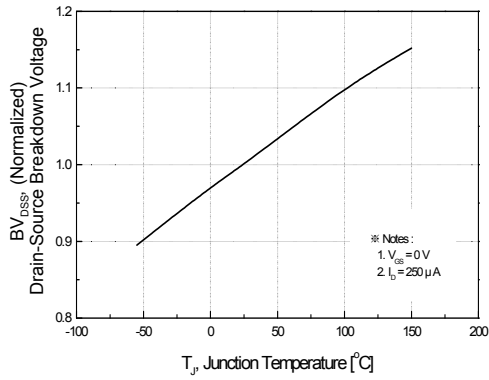


Figure 7. Breakdown Voltage Variation vs Temperature

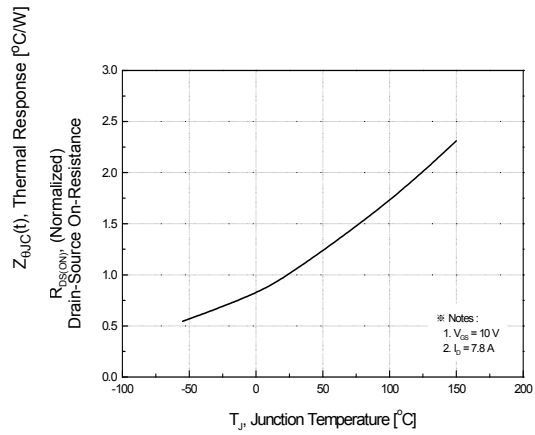


Figure 8. On-Resistance Variation vs Temperature

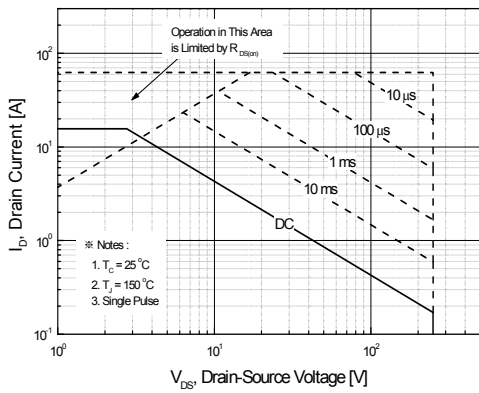


Figure 9. Maximum Safe Operating Area

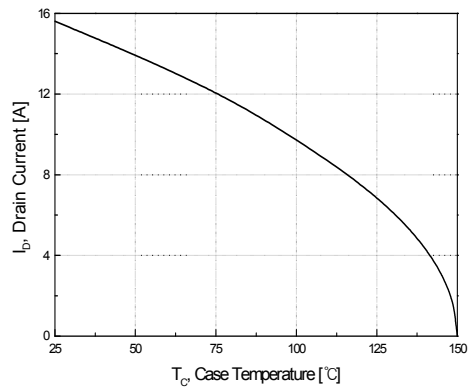


Figure 10. Maximum Drain Current vs Case Temperature

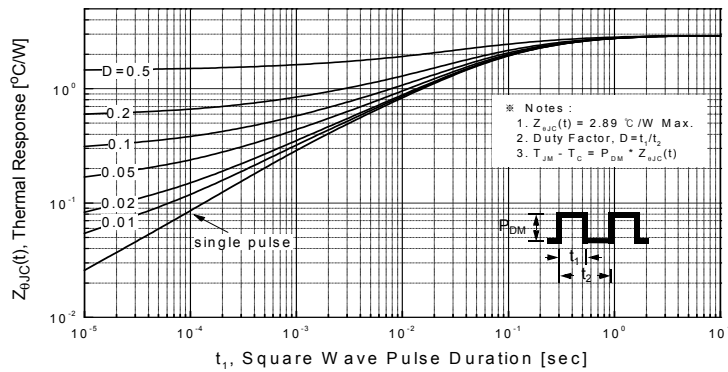


Figure 11. Transient Thermal Response Curve

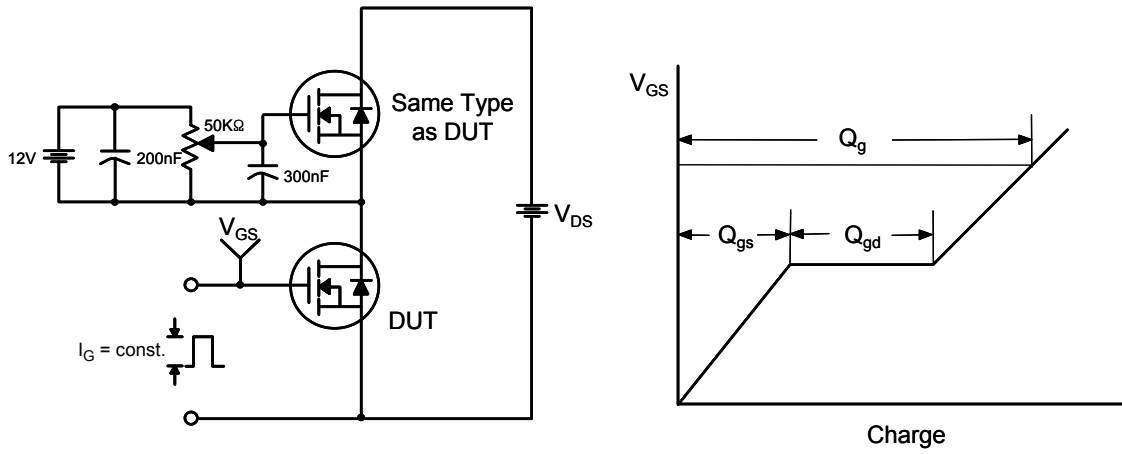


Figure 12. Gate Charge Test Circuit & Waveform

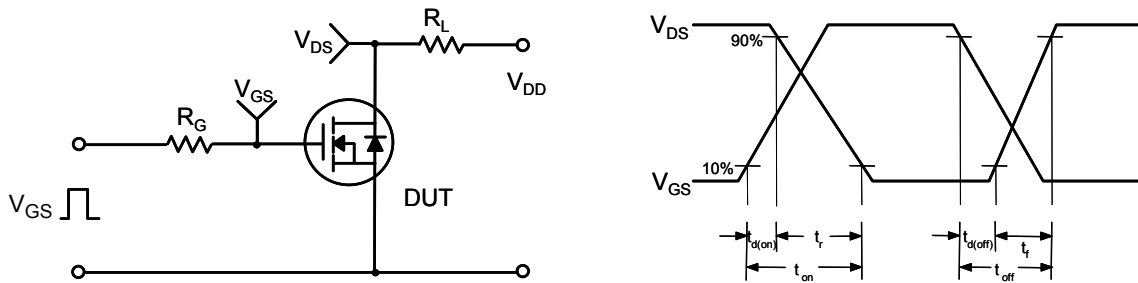


Figure 13. Resistive Switching Test Circuit & Waveforms

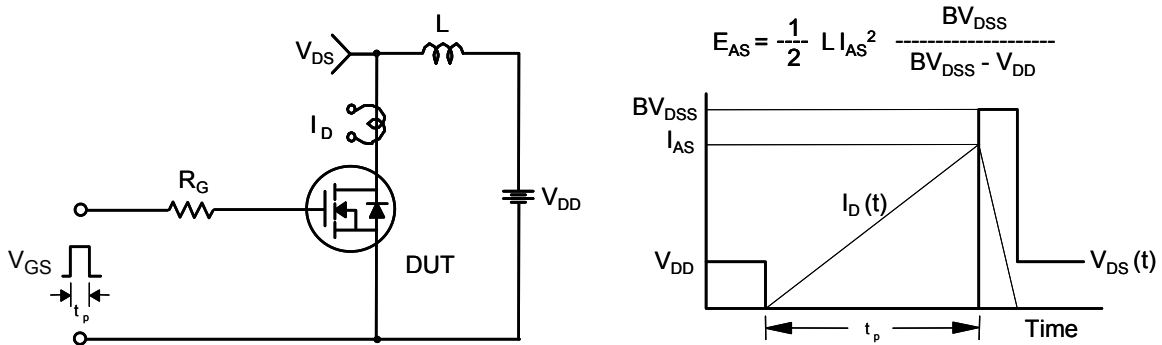


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

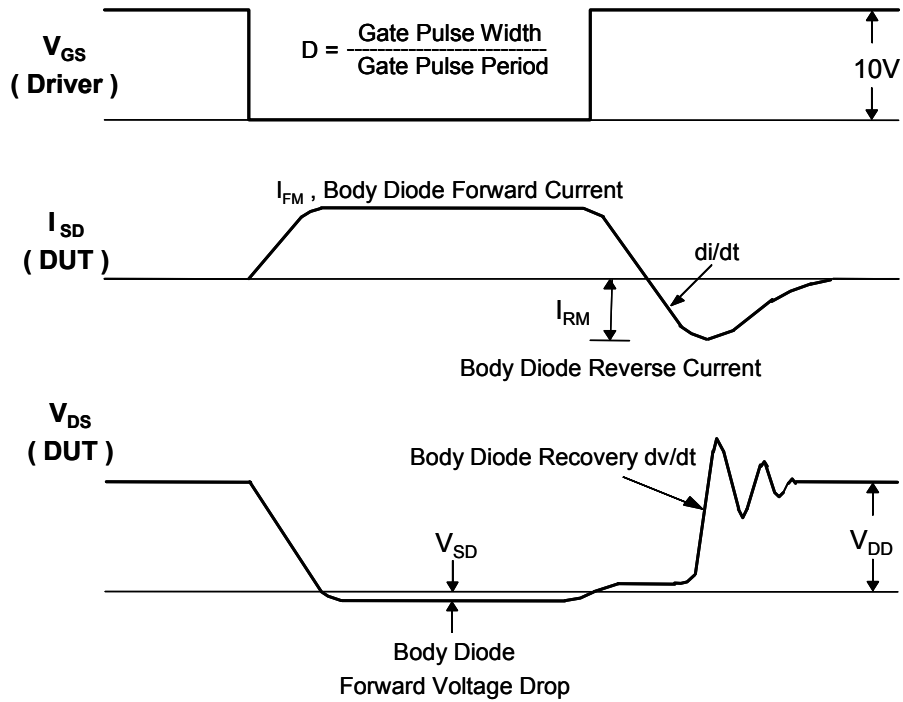
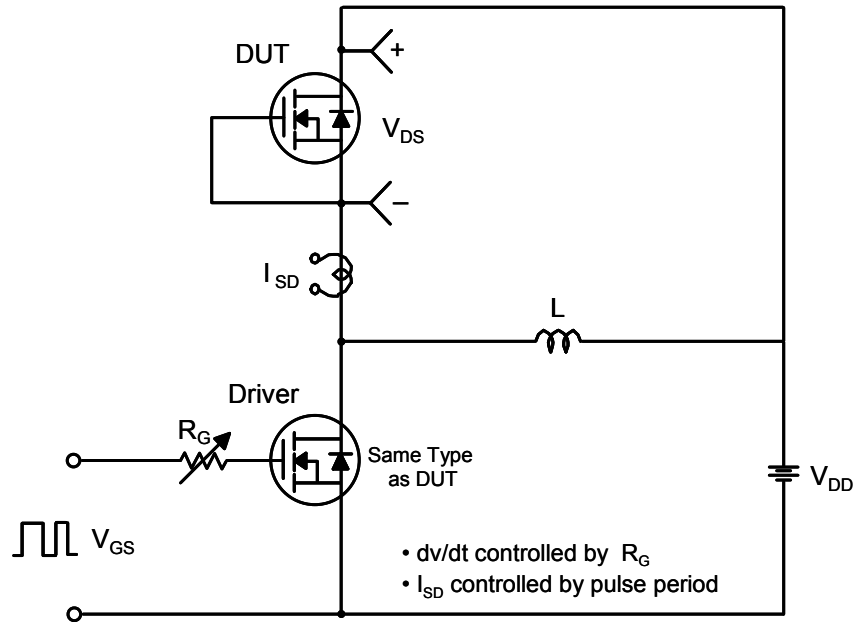


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3

Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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